



LVDS 4x4 CROSSPOINT SWITCH

FEATURES

- Greater Than 2.0 Gbps Operation
- Nonblocking Architecture Allows Each Output to be Connected to Any Input
- Pk-Pk Jitter:
 - 60 ps Typical at 2.0 Gbps
 - 110 ps Typical at 2.5 Gbps
- Compatible With ANSI TIA/EIA-644-A LVDS Standard
- Available Packaging 38-Pin TSSOP
- 25 mV of Input Voltage Threshold Hysteresis
- Propagation Delay Times: 800 ps Typical
- Inputs Electrically Compatible With LVPECL, CML and LVDS Signal Levels
- Operates From a Single 3.3-V Supply
- Low Power: 110 mA Typical
- Integrated 110- Ω Line Termination Resistors Available With SN65LVDT250

APPLICATIONS

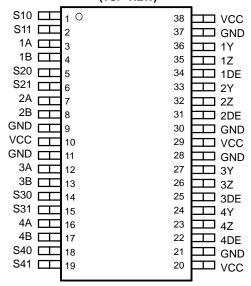
- Clock Buffering/Clock Muxing
- Wireless Base Stations
- High-Speed Network Routing
- Telecom/Datacom

DESCRIPTION

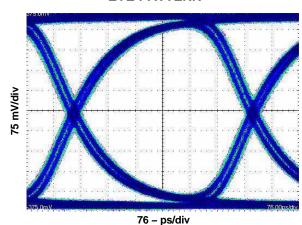
The SN65LVDS250 and SN65LVDT250 are 4x4 nonblocking crosspoint switches in a flow-through pin-out allowing for ease in PCB layout. Low-voltage differential signaling (LVDS) is used to achieve a high-speed data throughput while using low power. Each of the output drivers includes a 4:1 multiplexer to allow any input to be routed to any output. Internal signal paths are fully differential to achieve the high signaling speeds while maintaining low signal skews. The SN65LVDT250 incorporates $110\mbox{-}\Omega$ termination resistors for those applications where board space is a premium.

The SN65LVDS250 and SN65LVDT250 are characterized for operation from -40°C to 85°C.

SN65LVDS250DBT (Marked as LVDS250) SN65LVDT250DBT (Marked as LVDT250) (TOP VIEW)



EYE PATTERN



V_{IC}= 1.2 V |V_{ID}| = 200 mV 2 Gbps

Input = PRBS 2²³ -1 V_{CC} = 3.3 V



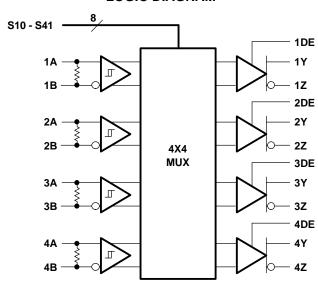
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

LOGIC DIAGRAM

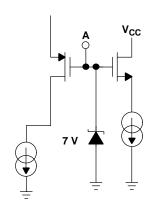


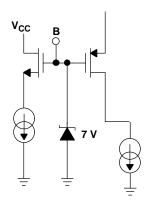
Integrated Termination on LVDT Only

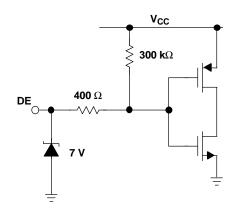


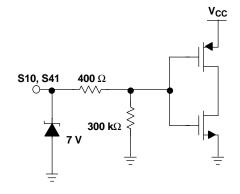
EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

INPUT LVDS250









OUTPUT LVDS250

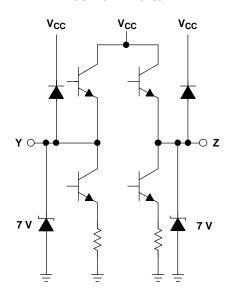




Table 1. CROSSPOINT LOGIC TABLES

Ol	OUTPUT CHANNEL 1			OUTPUT CHANNEL 2			OUTPUT CHANNEL 3			JTPUT C	HANNEL 4
	TROL NS	INPUT SELECTED		TROL NS	INPUT SELECTED	CONTROL PINS		INPUT SELECTED	CON.		INPUT SELECTED
S10	S11	1Y/1Z	S20	S21	2Y/2Z	S30	S31	3Y/3Z	S40	S41	4Y/4Z
0	0	1A/1B	0	0	1A/1B	0	0	1A/1B	0	0	1A/1B
0	1	2A/2B	0	1	2A/2B	0	1	2A/2B	0	1	2A/2B
1	0	3A/3B	1	0	3A/3B	1	0	3A/3B	1	0	3A/3B
1	1	4A/4B	1	1	4A/4B	1	1	4A/4B	1	1	4A/4B

PACKAGE DISSIPATION RATINGS

PACKAGE	CIRCUIT BOARD MODEL	T _A ≤ 25°C POWER RATING	DERATING FACTOR ⁽¹⁾ ABOVE T _A = 25°C	T _A = 85°C POWER RATING
TSSOP (DBT)	Low-K ⁽²⁾	1038 mW	9.0 mW/°C	496 mW
TSSOP (DBT)	High-K ⁽³⁾	1772 mW	15.4 mW/°C	847 mW

- (1) This is the inverse of the junction-to-ambient thermal resistance when board-mounded and with no air flow.
- (2) In accordance with the Low-K thermal metric definitions of EIA/JESD51-6
- (3) In accordance with the High-K thermal metric definitions of EIA/JESD51-6

THERMAL CHARACTERISTICS

PARAMETER TEST CONDITION		TEST CONDITIONS	VALUE	UNITS
Θ_{JB}	Junction-to-board thermal resistance		40.3	°C/W
$\Theta_{\sf JC}$	Junction-to-case thermal resistance		8.5	C/VV
D	Davisa naver dissination	V _{CC} = 3.3 V, T _A = 25°C, 1 GHz	356	mW
P _D	Device power dissipation	V _{CC} = 3.6 V, T _A = 85°C, 1 GHz	522	mW

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted (1)

			UNITS	
Supply voltage range, V _{CC}			-0.5 V to 4 V	
	S, DE		-0.5 V to 4 V	
Valtaga 200 (2)	А, В	A, B		
Voltage range ⁽²⁾	V _A - V _B (LVDT only)		1 V	
	Y, Z		-0.5 V to 4 V	
Flooting static disable and	Human body model ⁽³⁾	All pins	±3 kV	
Electrostatic discharge	Charged-device model ⁽⁴⁾	All pins	±500 V	
Continuous power dissipation	1		See Dissipation Rating Table	

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
- 3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.
- (4) Tested in accordance with JEDEC Standard 22, Test Method C101.



RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		3	3.3	3.6	V
V _{IH}	High-level input voltage	S10-S41, 1DE-4DE	2		V_{CC}	V
V _{IL}	Low-level input voltage	S10-S41, 1DE-4DE	0		0.8	V
157	Manaituda of differential insulturality as	LVDS	0.1		1	V
$ V_{ID} $	Magnitude of differential input voltage	LVDT	0.1		0.8	V
	Input voltage (any combination of common	-mode or input signals)	0		3.3	V
T_{J}	Junction temperature				140	°C
T _A (1)	Operating free-air temperature		-40		85	°C

⁽¹⁾ Maximum free-air temperature operation is allowed as long as the device maximum junction temperature is not exceeded.

TIMING SPECIFICATIONS

	PARAMETER		MIN	NOM	MAX	UNIT
t _{SET}	Input to select setup time			0.6		ns
t _{HOLD}	Input to select hold time	See Figure 7		0.2		ns
t _{SWITCH}	Select to switch output			1.2	1.6	ns

INPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted (1)

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IT+}	/ _{IT+} Positive-going differential input voltage threshold		See Figure 1			100	mV
V _{IT-}	Negative-going differential input voltag	e threshold	See Figure 1	-100			mV
V _{ID(HYS)}	Differential input voltage hysteresis				25		mV
	High level input suggest	1DE-4DE	V 2V	-10			
I _{IH}	High-level input current	S10-S41	V _{IH} = 2 V			20	μA
	Law law law at a sum at	1DE-4DE	V 00V	-10			
I _{IL}	Low-level input current	S10-S41	V _{IL} = 0.8 V			20	μA
I _I	Input current (A or B inputs)	ı	V _I = 0 V or 3.3 V, second input at 1.2 V (other input open for LVDT)	-20		20	μΑ
I _{I(OFF)}	Input current (A or B inputs)		$V_{CC} \le 1.5 \text{ V}, V_I = 0 \text{ V or } 3.3 \text{ V, second}$ input at 1.2 V(other input open for LVDT)	-20		20	μΑ
I _{IO}	Input offset current (I _{IA} - I _{IB}) (LVDS)		$V_{IA} = V_{IB, 0} \le V_{IA} \le 3.3 \text{ V}$	-6		6	μΑ
	Termination resistance (LVDT)		V _{ID} = 300 mV, V _{IC} = 0 V to 3.3 V	90	110	132	
R _T	Termination resistance (LVDT with pov	wer-off)	$V_{ID} = 300 \text{ mV}, V_{IC} = 0 \text{ V to } 3.3 \text{ V}, V_{CC} = 1.5 \text{ V}$	90	110	132	Ω
C _I	Differential input capacitance				2.5		pF

⁽¹⁾ All typical values are at 25°C and with a 3.3 V supply.



OUTPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{OD}	Differential output voltage magnitude	See Figure 2	247	350	454	mV
$\Delta V_{OD} $	Change in differential output voltage magnitude between logic states	$V_{ID} = \pm 100 \text{ mV}$	-50		50	mV
V _{OC(SS)}	Steady-state common-mode output voltage		1.125		1.375	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage between logic states	See Figure 3	-50		50	mV
V _{OC(PP)}	Peak-to-peak common-mode output voltage			50	150	mV
Icc	Supply current	R _L =100 Ω		110	145	mA
I _{OS}	Short-circuit output current	V_{OY} or $V_{OZ} = 0 V$	-27		27	mA
I _{OSD}	Differential short circuit output current	$V_{OD} = 0 V$	-12		12	mA
I _{OZ}	High-impedance output current	$V_O = 0 \text{ V or } V_{CC}$			±1	μA
Co	Differential output capacitance			2		pF

SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output		700	800	1200	
t _{PHL}	Propagation delay time, high-to-low-level output	Coo Figure 4	700	800	1200	20
t _r	Differential output signal rise time (20%-80%)	See Figure 4		200	245	ps
t _f	Differential output signal fall time (20%-80%)			200	245	
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH}) ⁽¹⁾			0	50	ps
t _{sk(o)}	Channel-to-channel output skew ⁽²⁾				175	ps
t _{sk(pp)}	Part-to-part skew ⁽³⁾				300	ps
t _{jit(per)}	Period jitter, rms (1 standard deviation) ⁽⁴⁾	See Figure 6		1	3	ps
t _{jit(cc)}	Cycle-to-cycle jitter (peak) ⁽⁵⁾	See Figure 6		8	17	ps
t _{jit(pp)}	Peak-to-peak jitteR (6)	See Figure 6		60	110	ps
t _{jit(det)}	Deterministic jitter, peak-to-peak ⁽⁷⁾	See Figure 6		48	65	ps
t _{PHZ}	Propagation delay, high-level-to-high-impedance output				6	
t _{PLZ}	Propagation delay, low-level-to-high-impedance output	Coo Figure F			6	20
t _{PZH}	Propagation delay, high-impedance -to-high-level output	See Figure 5			300	ns
t _{PZL}	Propagation delay, high-impedance-to-low-level output				300	

⁽¹⁾ $t_{sk(p)}$ is the magnitude of the time difference between the t_{PLH} and t_{PHL} of any output of a single device.

 $t_{sk(o)}$ is the maximum delay time difference between drivers over temperature, V_{CC} , and process.

 $t_{sk(p)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits. Input voltage = V_{ID} = 200 mV, 50% duty cycle at 1.0 GHz, t_r = t_r = 50 ps (20% to 80%), measured over 1000 samples. Input voltage = V_{ID} = 200 mV, 50% duty cycle at 1.0 GHz, t_r = t_r = 50 ps (20% to 80%). Input voltage = V_{ID} = 200 mV, 2²³-1 PRBS pattern at 2.0 Gbps, t_r = t_r = 50 ps (20% to 80%). Input voltage = V_{ID} = 200 mV, 2⁷-1 PRBS pattern at 2.0 Gbps, t_r = t_r = 50 ps (20% to 80%).



PARAMETER MEASUREMENT INFORMATION

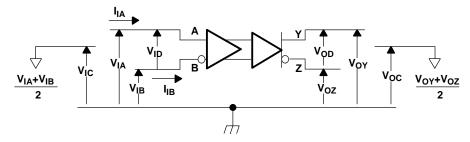


Figure 1. Voltage and Current Definitions

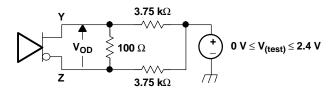
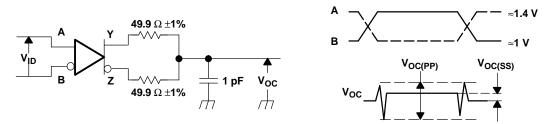
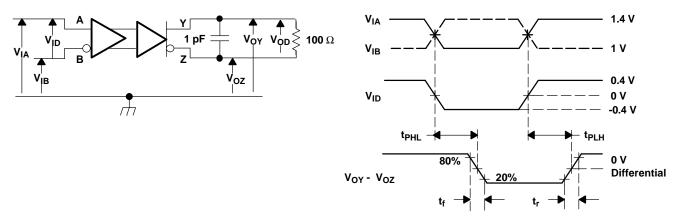


Figure 2. Differential Output Voltage (V_{OD}) Test Circuit



A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_i \le 1$ ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns; $R_L = 100\Omega$; C_L includes instrumentation and fixture capacitance within 0,06 mm of the DUT; the measurement of $V_{OC(PP)}$ is made on test equipment with a -3 dB bandwidth of at least 300 MHz

Figure 3. Test Circuit and Definitions fot the Driver Common-Mode Output Voltage

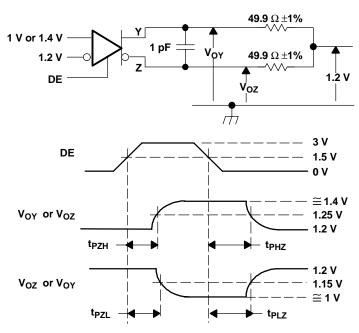


A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 0.25$ ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns . C_L includes instrumentation and fixture capacitance within 0,06 mm of the DUT.

Figure 4. Timing Test Circuit and Waveforms

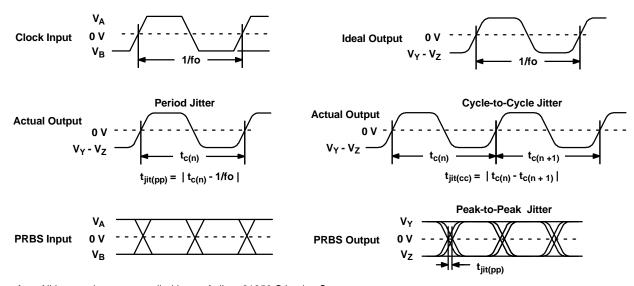


PARAMETER MEASUREMENT INFORMATION (continued)



A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_r \le 1$ ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns. C_L includes instrumentation and fixture capacitance within 0,06 mm of the DUT.

Figure 5. Enable and Disable Time Circuit and Definitions

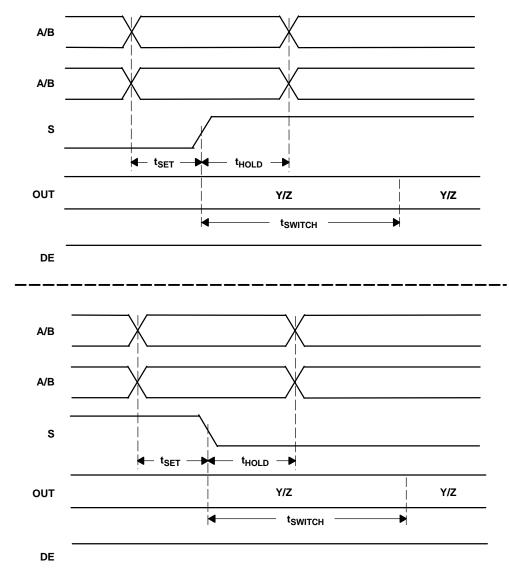


- A. All input pulses are supplied by an Agilent 81250 Stimulus System.
- B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software.

Figure 6. Driver Jitter Measurement Waveforms



PARAMETER MEASUREMENT INFORMATION (continued)



A. t_{SET} and t_{HOLD} times specify that data must be in a stable state before and after mux control switches.

Figure 7. Input to Select for Both Rising and Falling Edge Setup and Hold Times



TYPICAL CHARACTERISTICS

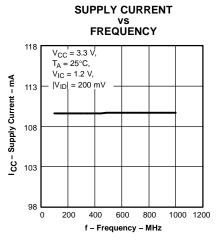


Figure 8.

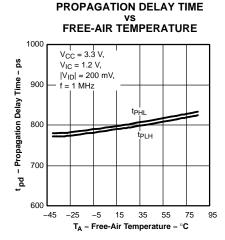
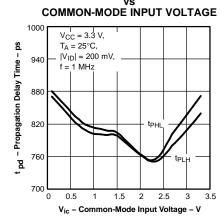


Figure 9.

PEAK-TO-PEAK JITTER



PROPAGATION DELAY TIME

Figure 10.

PEAK-TO-PEAK JITTER

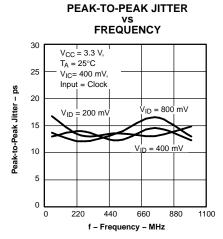


Figure 11.

PEAK-TO-PEAK JITTER

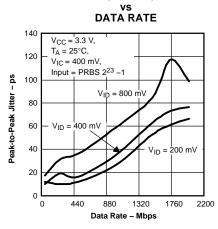


Figure 12.

PEAK-TO-PEAK JITTER

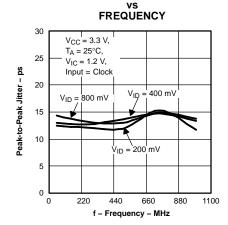


Figure 13.

PEAK-TO-PEAK JITTER

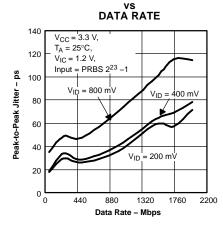


Figure 14.

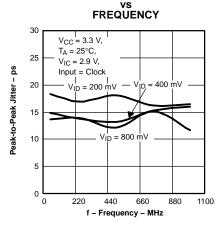


Figure 15.

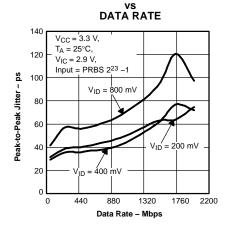


Figure 16.



TYPICAL CHARACTERISTICS (continued)



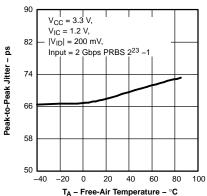


Figure 17.

DIFFERENTIAL OUTPUT VOLTAGE

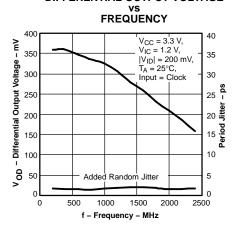


Figure 19.

PEAK-TO-PEAK JITTER vs DATA RATE

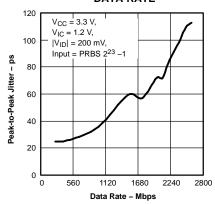
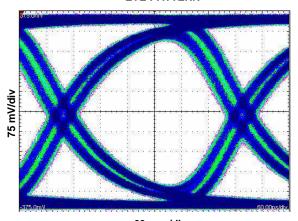


Figure 18.

EYE PATTERN



60 - ps/div $V_{IC} = 1.2 \text{ V}, \, |V_{ID}| = 200 \text{ mV}, \, 2.5 \text{ Gbps},$ $Input = PRBS \, 2^{23} - 1, \, V_{CC} = 3.3 \text{ V}$

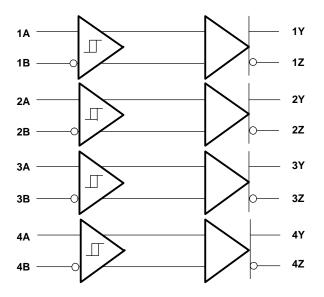
Figure 20.



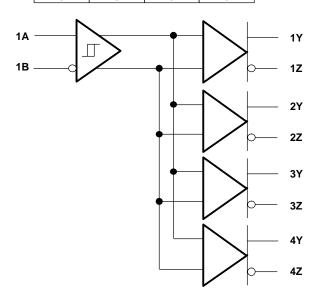
APPLICATION INFORMATION

CONFIGURATION EXAMPLES

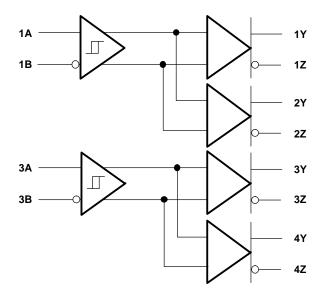
S10	S11	S20	S21
0	0	0	1
S30	S31	S40	S41
1	0	1	1



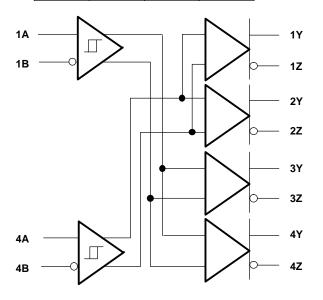
S10	S11	S20	S21
0	0	0	0
S30	S31	S40	S41
0	0	0	0



S10	S11	S20	S21
0	0	0	0
S30	S31	S40	S41
1	0	1	0



S10	S11	S20	S21
1	1	1	1
S30	S31	S40	S41
0	0	0	0





APPLICATION INFORMATION (continued)

TYPICAL APPLICATION CIRCUITS (ECL, PECL, LVDS, etc.)

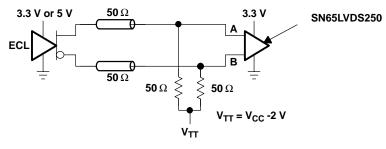


Figure 21. Low-Voltage Positive Emitter-Coupled Logic (LVPECL)

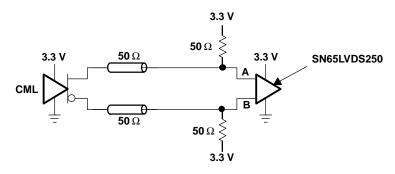


Figure 22. Current-Mode Logic (CML)

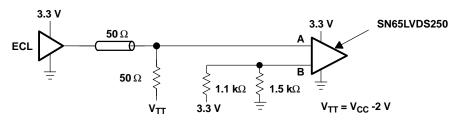


Figure 23. Single-Ended (LVPECL)

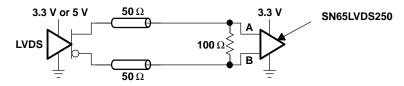


Figure 24. Low-Voltage Differential Signaling (LVDS)

www.ti.com 14-Oct-2022

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65LVDS250DBT	ACTIVE	TSSOP	DBT	38	50	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVDS250	Samples
SN65LVDS250DBTR	ACTIVE	TSSOP	DBT	38	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVDS250	Samples
SN65LVDT250DBT	ACTIVE	TSSOP	DBT	38	50	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVDT250	Samples
SN65LVDT250DBTR	ACTIVE	TSSOP	DBT	38	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVDT250	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and



PACKAGE OPTION ADDENDUM

www.ti.com 14-Oct-2022

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Dec-2023

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVDS250DBTR	TSSOP	DBT	38	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1
SN65LVDT250DBTR	TSSOP	DBT	38	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Dec-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDS250DBTR	TSSOP	DBT	38	2000	350.0	350.0	43.0
SN65LVDT250DBTR	TSSOP	DBT	38	2000	350.0	350.0	43.0

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Dec-2023

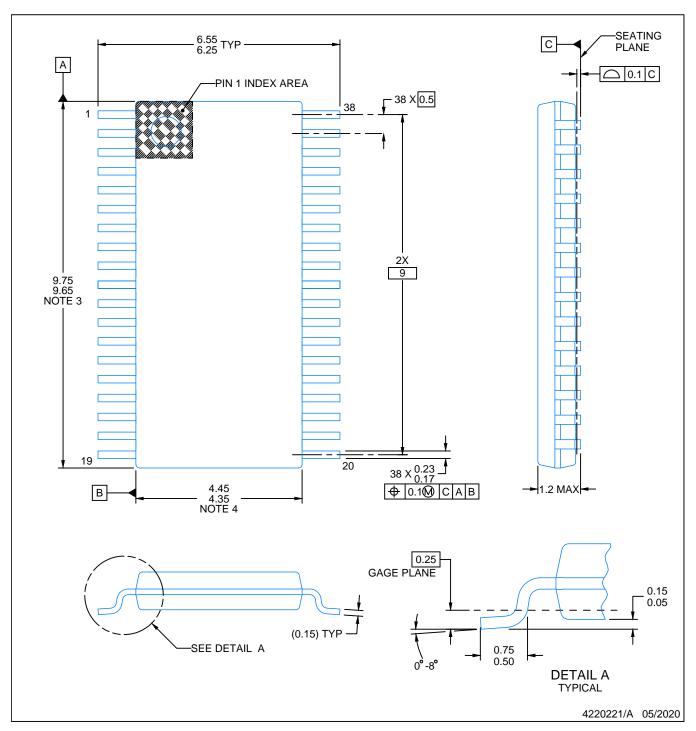
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65LVDS250DBT	DBT	TSSOP	38	50	530	10.2	3600	3.5
SN65LVDT250DBT	DBT	TSSOP	38	50	530	10.2	3600	3.5

SMALL OUTLINE PACKAGE

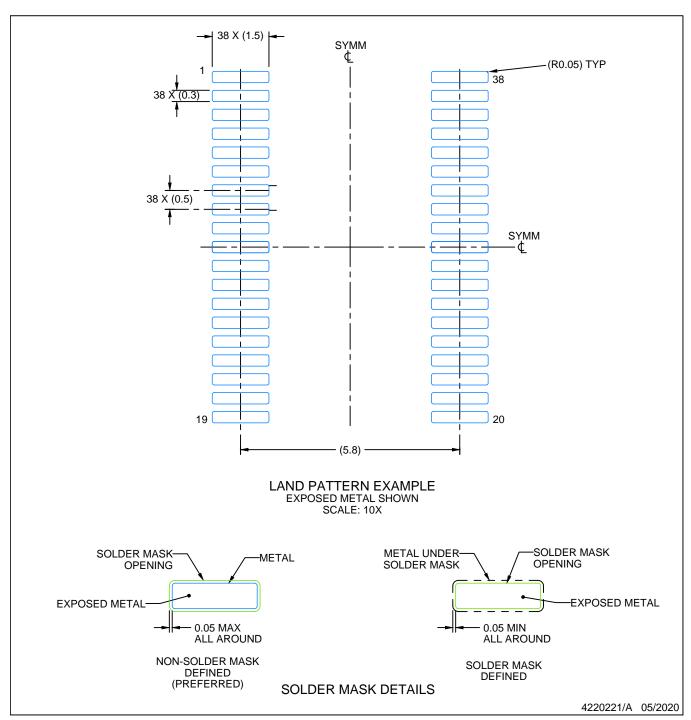


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



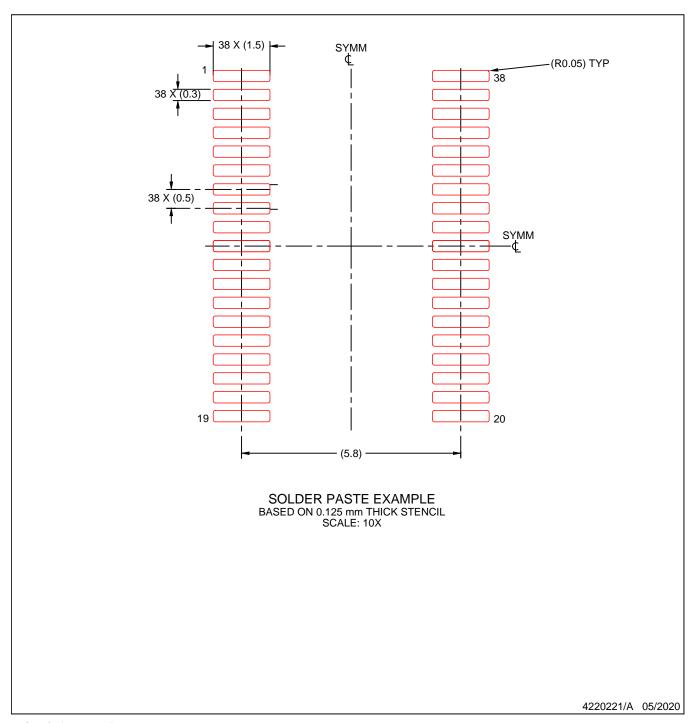
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2023, Texas Instruments Incorporated